



# SSC8L410GN6

## N-Channel Enhanced MOSFET

### ➤ Features

VDS	VGS	RDSON Typ.	ID
40V	±20V	4.5mΩ@10V	61A
		6mΩ@4V5	

### ➤ Description

This device is N-Channel enhancement MOSFET. Uses SGT technology and design to provide excellent RDSON with low gate charge. This device is suitable for use in DC-DC conversion, power switch and charging circuit.

100% UIS + ΔVDS + Rg Tested.

### ➤ Applications

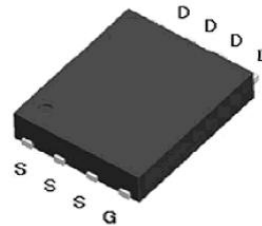
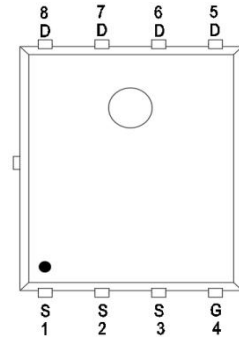
- DC/DC converters
- Power supplies
- Motor Drive Control
- Synchronous rectification

### ➤ Ordering Information

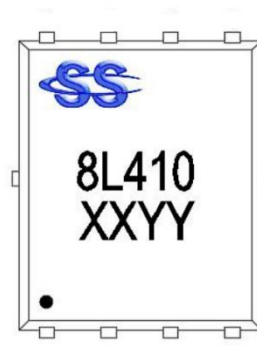
Device	Package	Shipping
SSC8L410GN6	PDFN5X6	5000/Reel

### ➤ Pin configuration

Top view



PDFN5X6



Marking

(XX: product year / YY: product week)

➤ **Absolute Maximum Ratings**( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

Symbol	Parameter	Ratings	Unit
$V_{DSS}$	Drain-to-Source Voltage	40	V
$V_{GSS}$	Gate-to-Source Voltage	$\pm 20$	V
$I_D$	Continuous Drain Current <sup>d</sup>	$T_C=25^{\circ}\text{C}$	61
		$T_C=100^{\circ}\text{C}$	31
$I_{DSM}$	Continuous Drain Current <sup>a</sup>	$T_A=25^{\circ}\text{C}$	23
		$T_A=70^{\circ}\text{C}$	16
$I_{DM}$	Pulsed Drain Current <sup>b</sup>	244	A
$P_D$	Power Dissipation <sup>c</sup>	$T_C=25^{\circ}\text{C}$	27
		$T_C=100^{\circ}\text{C}$	11
$P_{DSM}$	Power Dissipation <sup>a</sup>	$T_A=25^{\circ}\text{C}$	4.2
		$T_A=70^{\circ}\text{C}$	2.7
$I_{AS}$	Avalanche Current <sup>b</sup> L=0.5mH Single Pulse	23	A
$E_{AS}$	Avalanche Energy <sup>b</sup> L=0.5mH Single Pulse	132	mJ
$T_J$	Operation junction temperature	-55~150	$^{\circ}\text{C}$
$T_{STG}$	Storage temperature range	-55~150	

➤ **Thermal Resistance Ratings**( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

Symbol	Parameter	Ratings	Unit
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance <sup>a</sup>	30	$^{\circ}\text{C}/\text{W}$
$R_{\theta JC}$	Junction-to-Case Thermal Resistance	4.5	

Note:

- The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz.copper, in a still air environment with  $T_A=25^{\circ}\text{C}$ . The value in any given application depends on the user is specific board design. The power dissipation is based on the  $t \leq 10\text{s}$  thermal resistance rating.
- Repetitive rating, pulse width limited by junction temperature.
- The power dissipation  $P_D$  is based on  $T_{J(MAX)}=150^{\circ}\text{C}$ , using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.
- The maximum current rating is package limited.



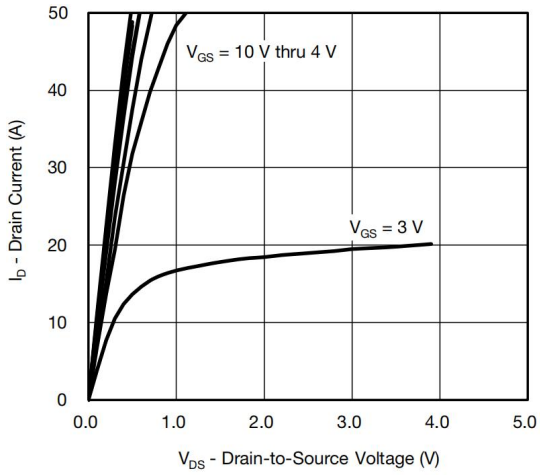
## SSC8L410GN6

➤ **Electronics Characteristics**( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

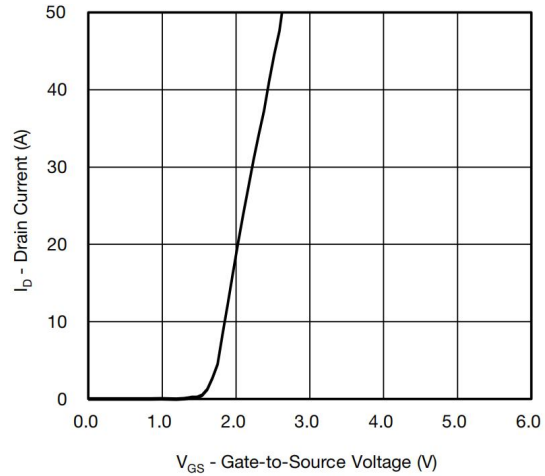
Symbol	Parameter	Test Conditions	Min	Typ.	Max	Unit
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	40			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.4	2.0	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10V, I_D=20A$		4.5	6.5	m $\Omega$
		$V_{GS}=4.5V, I_D=10A$		6	9	
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=40V, V_{GS}=0V$			1	$\mu A$
$I_{GSS}$	Gate-Source leak current	$V_{GS}=\pm 20V, V_{DS}=0V$			$\pm 150$	nA
$G_{FS}$	Transconductance	$V_{DS}=5V, I_D=20A$		16		S
$V_{SD}$	Forward Voltage	$V_{GS}=0V, I_S=10A$		0.77	1.3	V
$R_g$	Gate Resistance	$V_{DS}=0V, f=1MHz$		1.6		$\Omega$
$C_{iss}$	Input Capacitance	$V_{DS}=20V, V_{GS}=0V, f=1MHz$		1400		pF
$C_{oss}$	Output Capacitance			352		
$C_{rss}$	Reverse Capacitance			31		
$T_{D(ON)}$	Turn-on delay time	$V_{GS}=10V, R_L=1\Omega, V_{DS}=20V, R_G=3\Omega$		10		ns
$T_r$	Rise time			4		
$T_{D(OFF)}$	Turn-off delay time			25		
$T_f$	Fall time			5		
$Q_G$	Total Gate Charge	$V_{GS}=10V, V_{DS}=20V, I_D=20A$		27.3		nC
$Q_{GS}$	Gate Source Charge			4		
$Q_{GD}$	Gate Drain Charge			5.8		
$T_{rr}$	Diode Recovery Time	$I_F=20A, di/dt=500A/\mu s$		14		ns
$Q_{rr}$	Diode Recovery Charge	$I_F=20A, di/dt=500A/\mu s$		25		nC



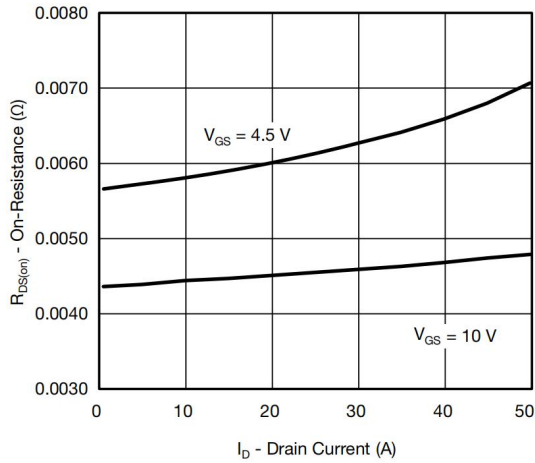
➤ **Typical Characteristics** ( $T_A=25^\circ\text{C}$  unless otherwise noted)



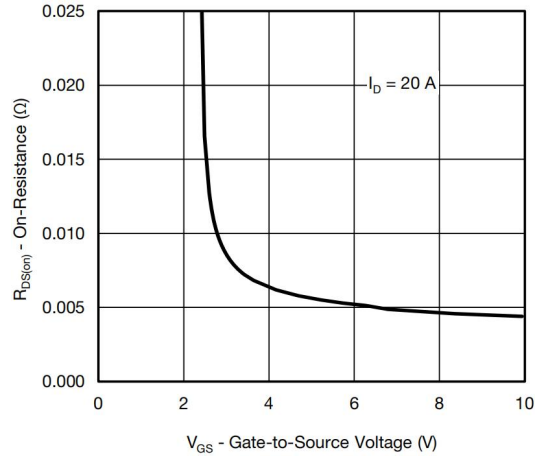
**Output Characteristics**



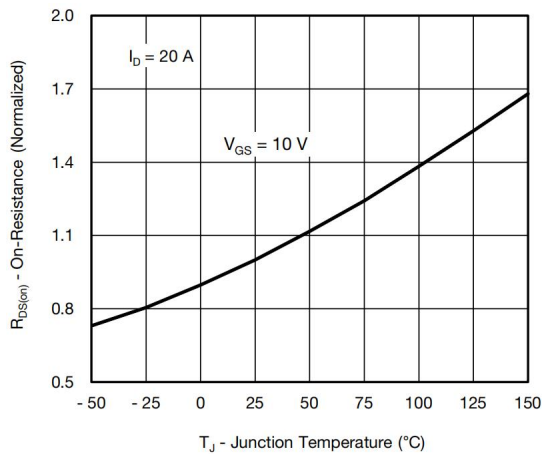
**Transfer Characteristics**



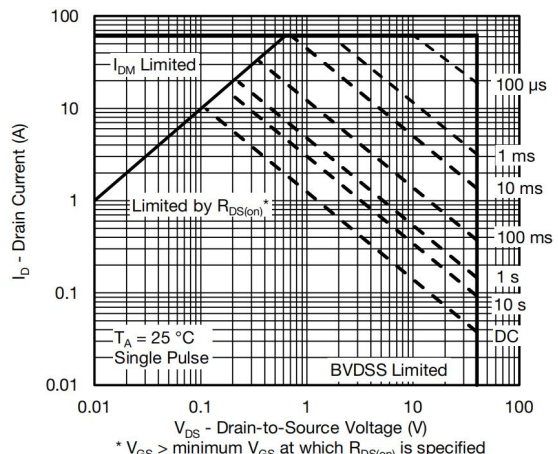
**On-Resistance vs. Drain Current and Gate Voltage**



**On-Resistance vs. Gate-to-Source Voltage**



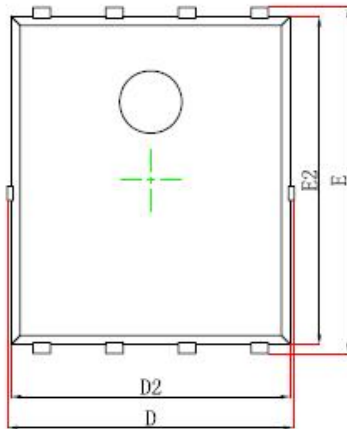
**On-Resistance vs. Junction Temperature**



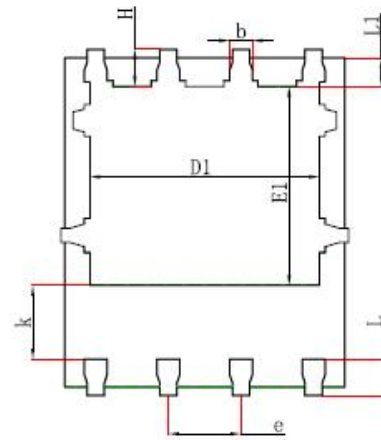
**Safe Operating Area, Junction-to-Ambient**



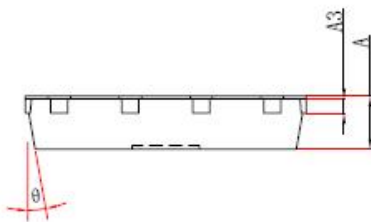
➤ Package Information



Top View  
[顶视图]



Bottom View  
[背视图]



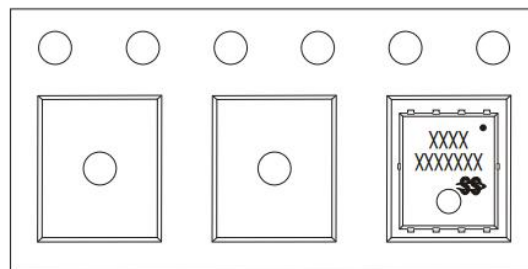
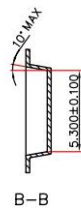
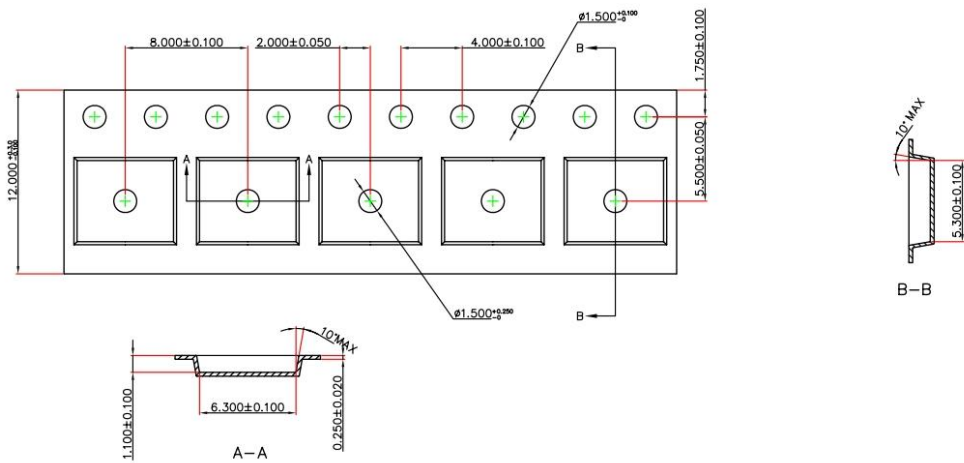
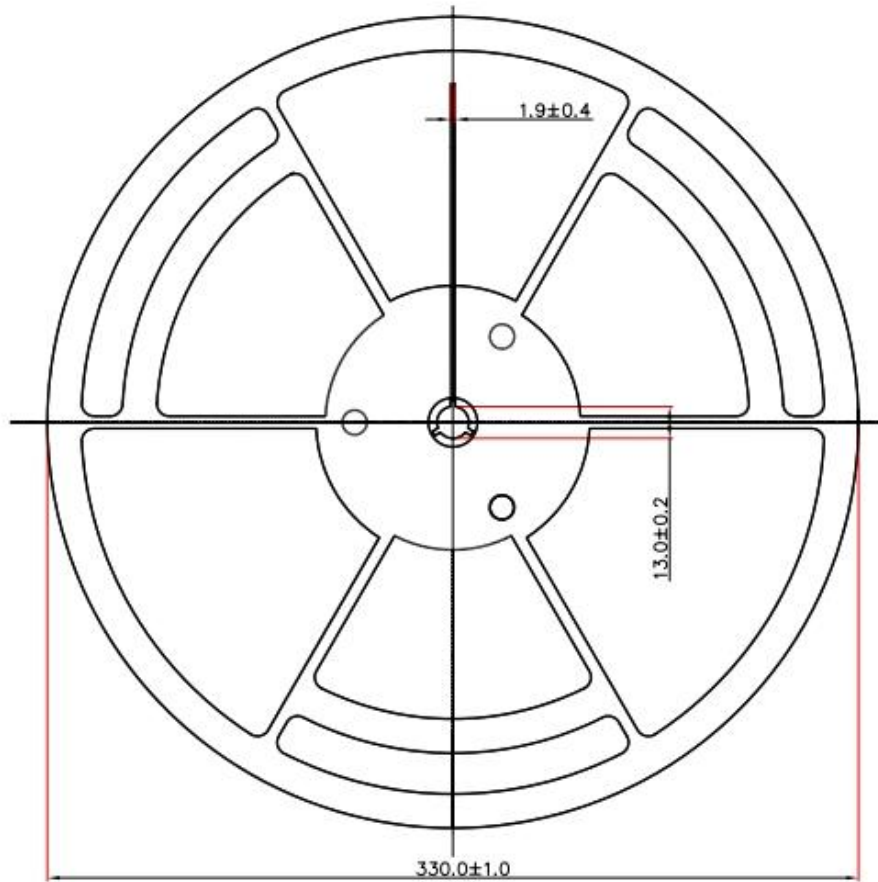
Side View  
[侧视图]

Package: PDNF5X6-8L

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254REF		0.010REF	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	3.910	4.110	0.154	0.162
E1	3.375	3.575	0.133	0.141
D2	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP		0.050TYP	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	10°	12°	10°	12°



➤ Tape and Reel





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